

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	EVBAS70-S1, EVBAS70-XX-S1
▶ Overseas	Part Number	BAS70, BAS70-XX
▶ Equivalent	Part Number	BAS70, BAS70-XX

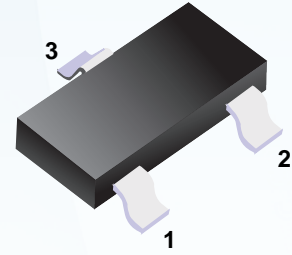
"S1" means SOT-23

EV is the abbreviation of name EVVO

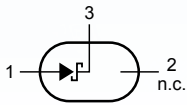
■ Schottky Diodes

■ Features

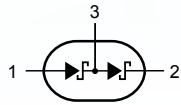
- Fast Switching Speed
- High breakdown voltage



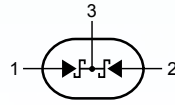
■ Simplified outline(SOT-23)



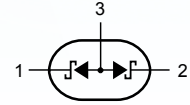
EVBAS70-S1 single diode.



EVBAS70-04-S1



EVBAS70-05-S1



EVBAS70-06-S1

■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Reverse Voltage	V _{RM}	70	V
Peak Reverse Voltage	V _{RRM}	70	
Average Rectified Current at Temp=25°C	I _{FAV}	70	mA
Non-Repetitive Peak Forward Surge Current t=1s	I _{FSM}	100	
Power Dissipation	P _d	215	mW
Thermal Resistance Junction to Ambient	R _{θJA}	500	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

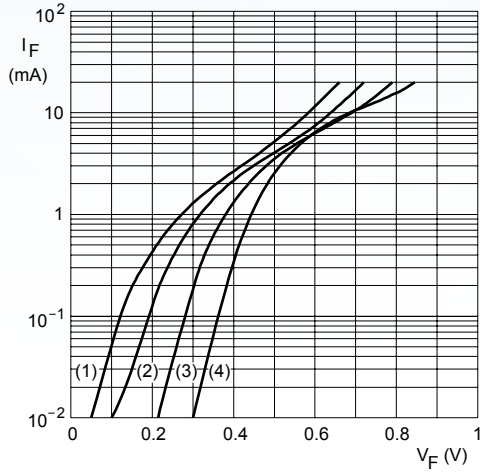
■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V _R	I _R = 10 uA	70			V
Forward voltage	V _{F1}	I _F = 1 mA			0.41	
	V _{F2}	I _F = 10 mA			0.75	
	V _{F3}	I _F = 15 mA			1	
Reverse voltage leakage current	I _{R1}	V _R = 70 V			1	uA
	I _{R2}	V _R = 50 V			0.1	
Junction capacitance	C _j	V _R = 0 V, f= 1 MHz			2	pF

■ Marking

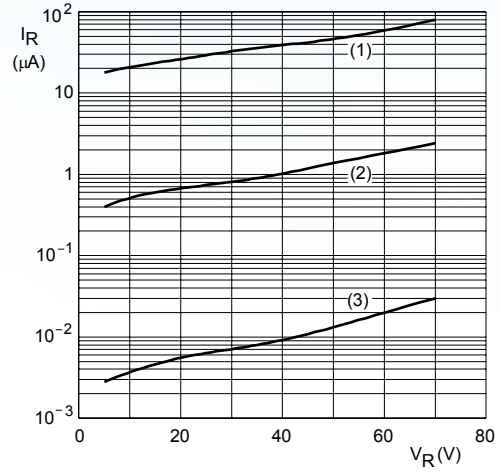
NO.	EVBAS70-S1	EVBAS70-04-S1	EVBAS70-05-S1	EVBAS70-06-S1
Marking	73	74	75	76

■ Typical Characteristics



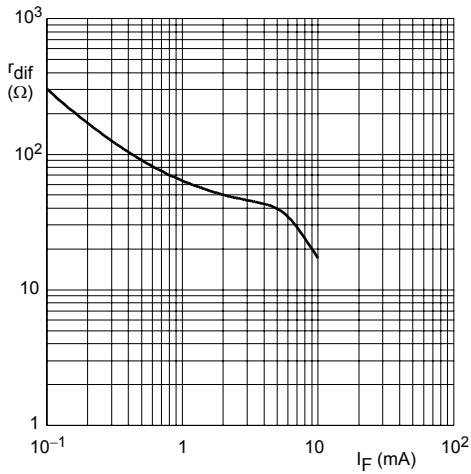
- (1) $T_{\text{amb}} = 125^\circ\text{C}$.
- (2) $T_{\text{amb}} = 85^\circ\text{C}$.
- (3) $T_{\text{amb}} = 25^\circ\text{C}$.
- (4) $T_{\text{amb}} = -40^\circ\text{C}$.

Fig.1 Forward current as a function of forward voltage; typical values.



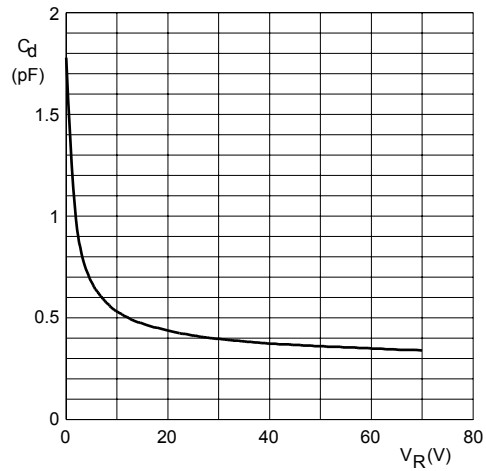
- (1) $T_{\text{amb}} = 150^\circ\text{C}$.
- (2) $T_{\text{amb}} = 85^\circ\text{C}$.
- (3) $T_{\text{amb}} = 25^\circ\text{C}$.

Fig.2 Reverse current as a function of reverse voltage; typical values.



f = 10 kHz.

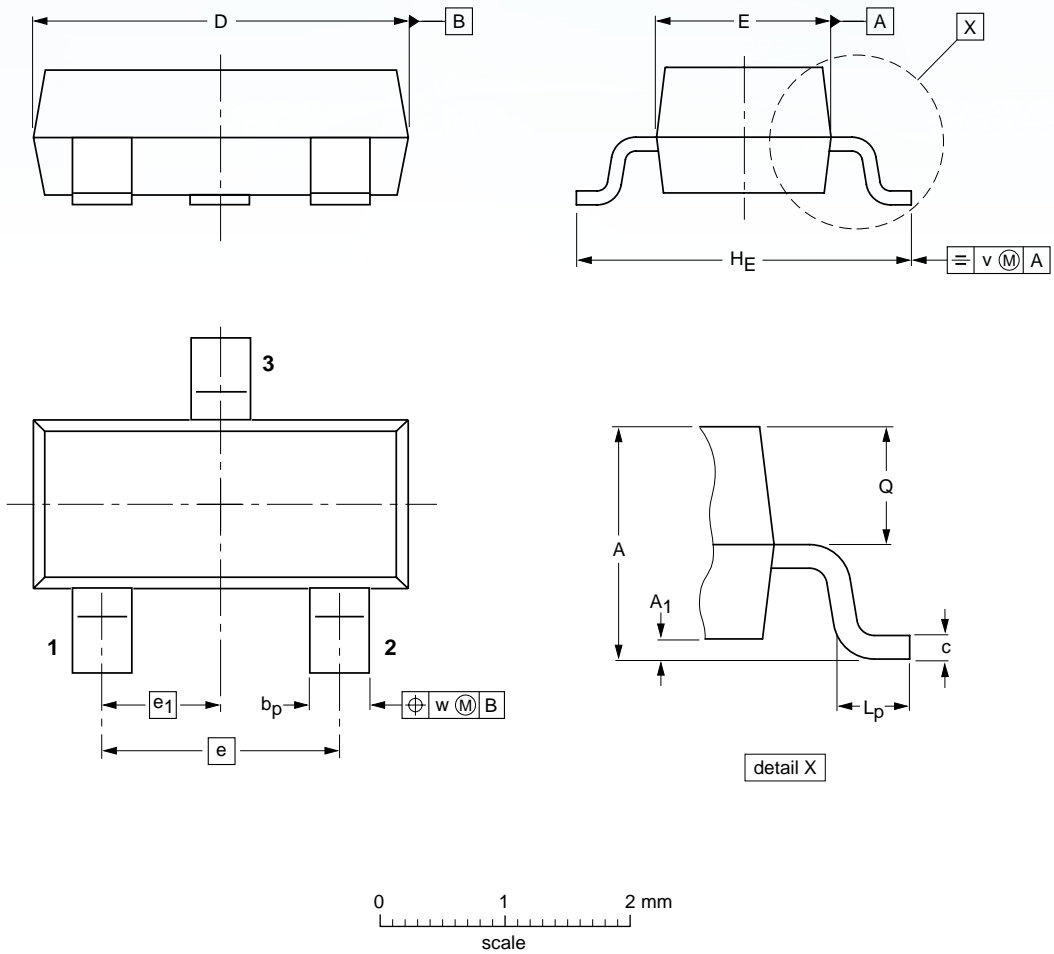
Fig.3 Differential forward resistance as a function of forward current; typical values.



f = 1 MHz.

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

■ SOT-23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

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